

isc Silicon PNP Power Transistor

2SB995

DESCRIPTION

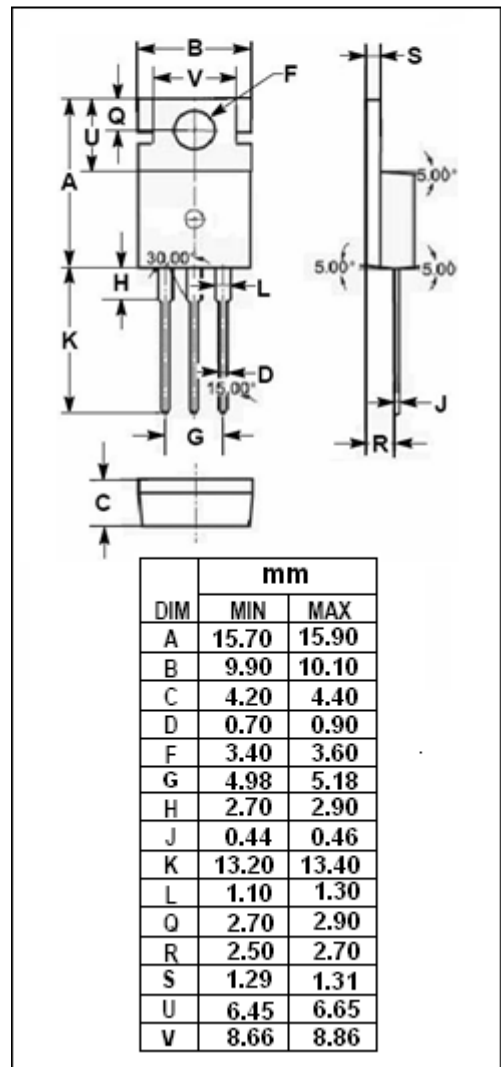
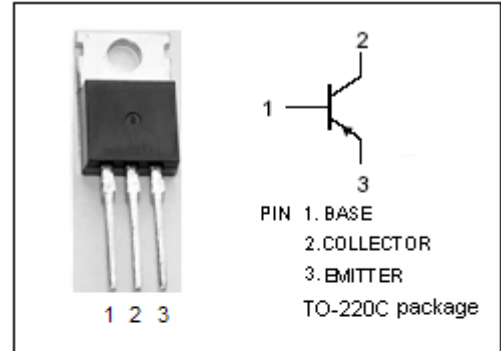
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -2.0V(\text{Max}) @ I_C = -4A$
- Complement to Type 2SD1355

APPLICATIONS

- Power amplifier applications.
- Recommended for 30W high-fidelity audio frequency amplifier output stage.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-5	A
I_B	Base Current-Continuous	-0.5	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SB995****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; I _B = 0	-100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -4A; I _B = -0.4A			-2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -4A; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-1.0	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -5V	40		240	
h _{FE-2}	DC Current Gain	I _C = -4A; V _{CE} = -5V	20			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		270		pF
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		5		MHz

◆ **h_{FE-1} Classifications**

R	O	Y
40-80	70-140	120-240